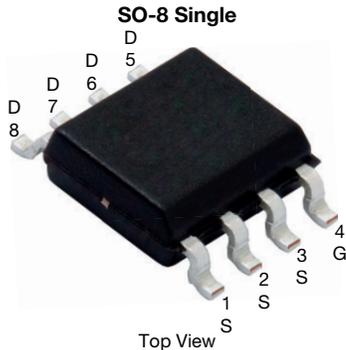


## N-Channel 60 V (D-S) MOSFET



### FEATURES

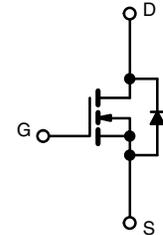
- TrenchFET® Gen IV power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Synchronous rectification
- Primary side switch
- DC/DC converters
- Power supplies
- Motor drive control
- Battery and load switch



N-Channel MOSFET

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	60
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 10 V	0.0195
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 4.5 V	0.0250
Q <sub>g</sub> typ. (nC)	5.2
I <sub>D</sub> (A)	11.3
Configuration	Single

### ORDERING INFORMATION

Package	SO-8
Lead (Pb)-free and halogen-free	Si4850BDY-T1-GE3

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V <sub>DS</sub>	60	V
Gate-source voltage	V <sub>GS</sub>	± 20	V
Continuous drain current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	11.3
		T <sub>C</sub> = 70 °C	9
		T <sub>A</sub> = 25 °C	8.4 a, b
		T <sub>A</sub> = 70 °C	6.8 a, b
Pulsed drain current (t = 100 μs)	I <sub>DM</sub>	40	A
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	3.8
		T <sub>A</sub> = 25 °C	2.1 a, b
Single pulse avalanche current	I <sub>AS</sub>	15	
Single pulse avalanche energy	E <sub>AS</sub>	11.3	mJ
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	4.5
		T <sub>C</sub> = 70 °C	2.8
		T <sub>A</sub> = 25 °C	2.5 a, b
		T <sub>A</sub> = 70 °C	1.6 a, b
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>c</sup>		260	

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a</sup>	R <sub>thJA</sub>	38	50	°C/W
Maximum junction-to-foot (drain)	R <sub>thJF</sub>	22	28	

#### Notes

- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- Maximum under steady state conditions is 85 °C/W



SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	33	-	mV/ $^\circ\text{C}$
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	-4.8	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	-	2.8	V
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	100	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$	-	-	10	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	10	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	0.0160	0.0195	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	-	0.0200	0.0250	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$	-	39	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{ISS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	790	-	pF
Output capacitance	$C_{OSS}$		-	330	-	
Reverse transfer capacitance	$C_{RSS}$		-	14	-	
Total gate charge	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	-	11.1	17	nC
		$V_{DS} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	-	5.2	8	
Gate-source charge	$Q_{gs}$		-	2.2	-	
Gate-drain charge	$Q_{gd}$		-	1.1	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.1	0.6	1.2	$\Omega$
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 6\text{ }\Omega, I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	7	15	ns
Rise time	$t_r$		-	21	40	
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	$t_f$		-	10	20	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 6\text{ }\Omega, I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$	-	13	25	
Rise time	$t_r$		-	25	50	
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	$t_f$		-	22	45	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	3.8	A
Pulse diode forward current	$I_{SM}$		-	-	40	
Body diode voltage	$V_{SD}$	$I_S = 5\text{ A}, V_{GS} = 0\text{ V}$	-	0.79	1.2	V
Body diode reverse recovery time	$t_{rr}$	$I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	-	30	60	ns
Body diode reverse recovery charge	$Q_{rr}$		-	60	120	nC
Reverse recovery fall time	$t_a$		-	15	-	ns
Reverse recovery rise time	$t_b$		-	15	-	

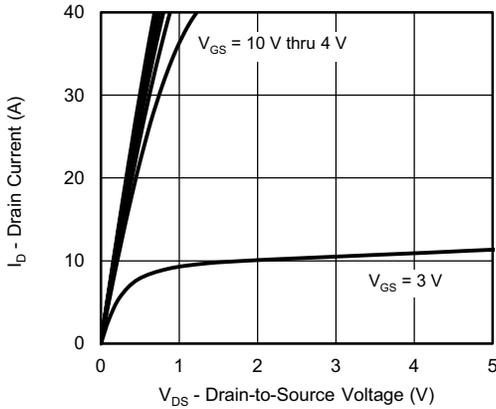
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

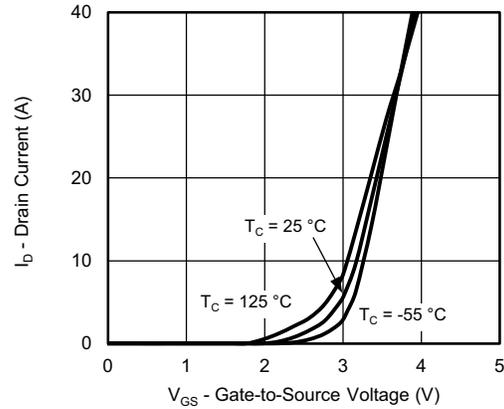
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



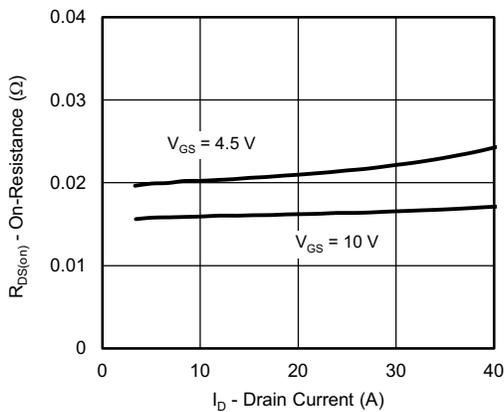
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



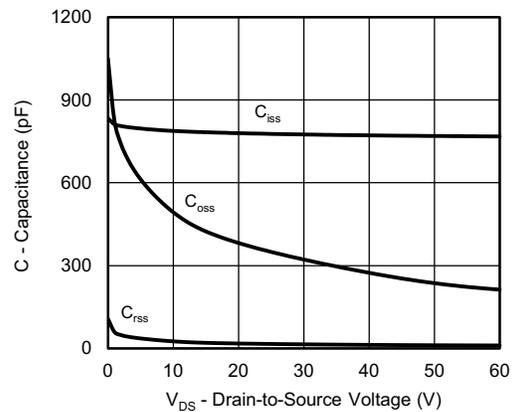
Output Characteristics



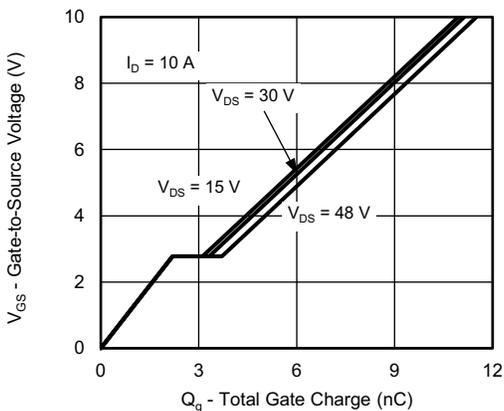
Transfer Characteristics



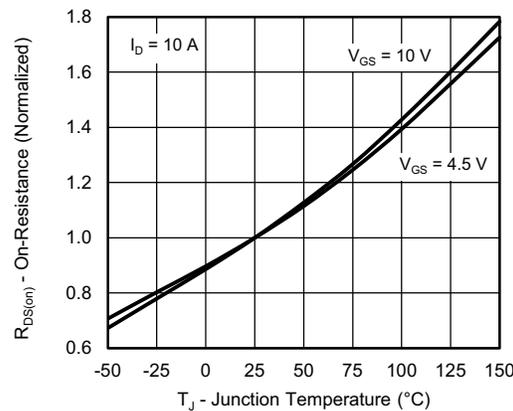
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



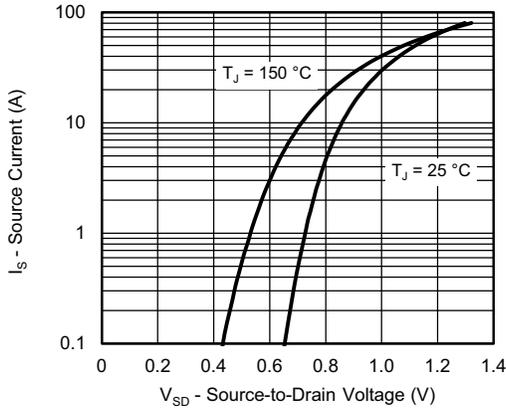
Gate Charge



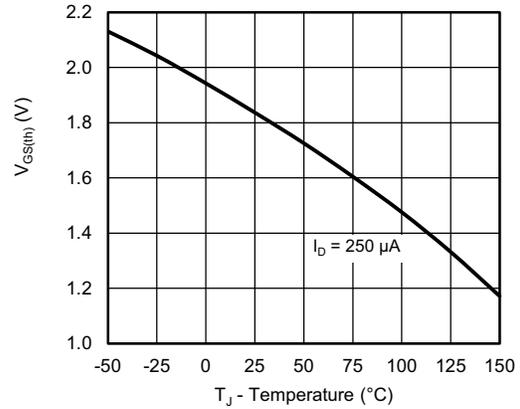
On-Resistance vs. Junction Temperature



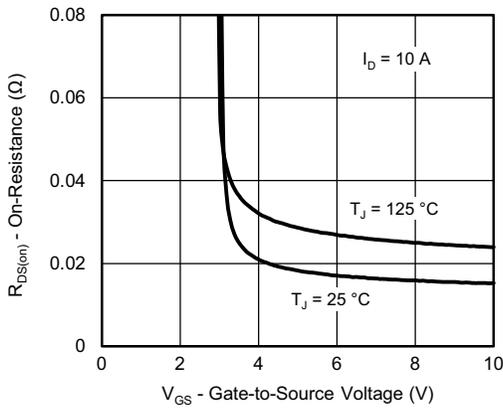
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



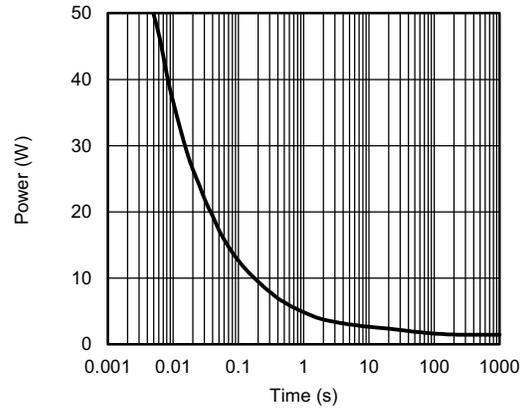
**Source-Drain Diode Forward Voltage**



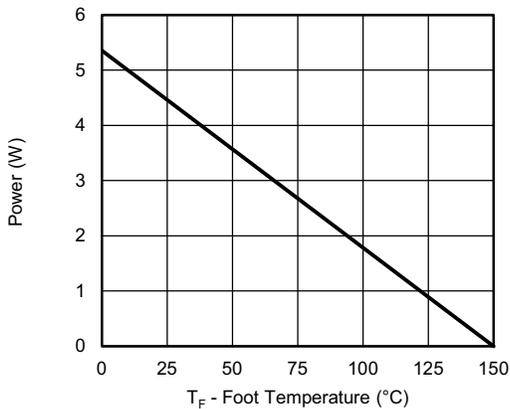
**Threshold Voltage**



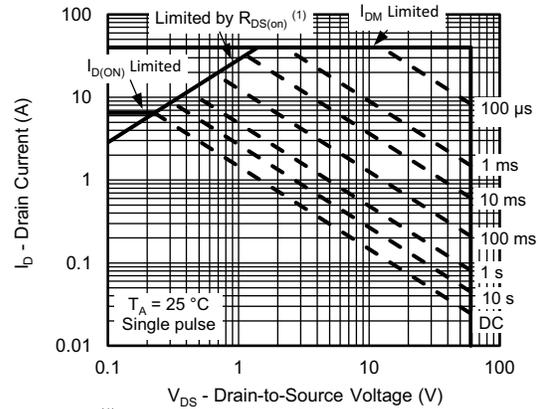
**On-Resistance vs. Gate-to-Source Voltage**



**Single Pulse Power, Junction-to-Ambient**

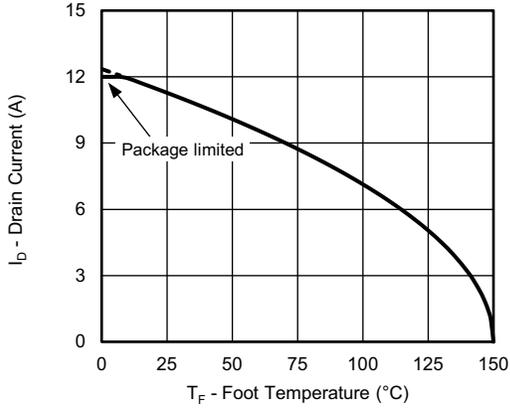


**Power, Junction-to-Foot**



**Safe Operating Area, Junction-to-Ambient**

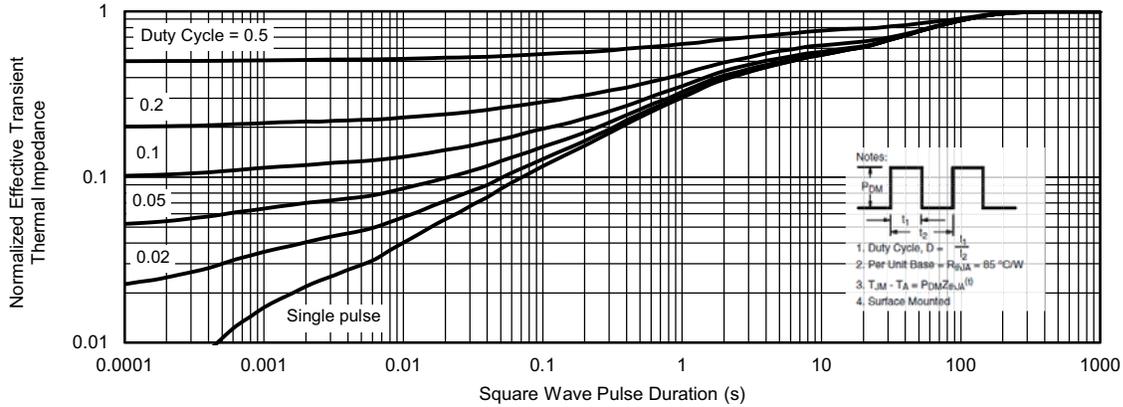
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



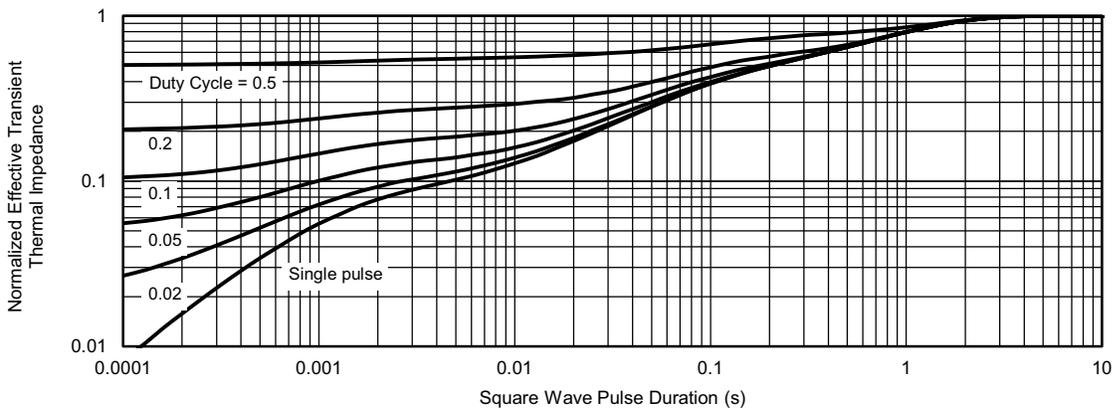
**Note**

a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**Current Derating <sup>a</sup>**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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